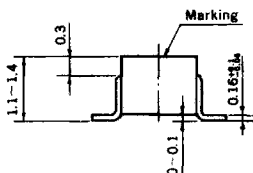
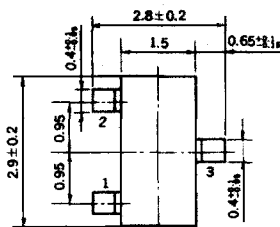


SILICON SWITCHING DIODES

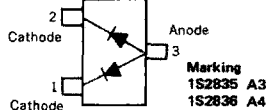
1S2835, 1S2836

SILICON EPITAXIAL DOUBLE DIODES : COMMON ANODE HIGH SPEED SWITCHING MINI MOLD

PACKAGE DIMENSIONS



Connection Diagram (Top View)



FEATURES

- Low capacitance: $C_t = 2.5 \text{ pF TYP.}$
- High speed switching: $t_{rr} = 4.0 \text{ ns MAX.}$
- Wide applications including switching, limiter, clipper.
- Double diode configuration assures economical use.

ABSOLUTE MAXIMUM RATINGS

Maximum Voltages and Currents ($T_a = 25^\circ\text{C}$)

		1S2835	1S2836	
Peak Reverse Voltage	V_{RM}	35	75	V
DC Reverse Voltage	V_R	30	50	V
Surge Current (1 μ s)*	I_{FSM}	6.0	6.0	A
Surge Current (1 μ s)	I_{FSM}	4.0	4.0	A
Peak Forward Current*	I_{FM}	450	450	mA
Peak Forward Current	I_{FM}	300	300	mA
Average Rectified Current*	I_O	150	150	mA
Average Rectified Current	I_O	100	100	mA

Maximum Temperatures

Junction Temperature	T_j	125	125	$^{\circ}\text{C}$
Storage Temperature Range	T_{sto}	-55 to +125	-55 to +125	$^{\circ}\text{C}$

Thermal Resistance

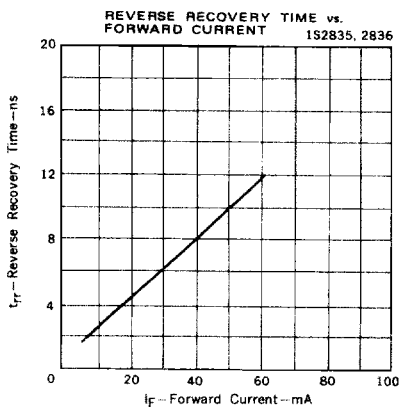
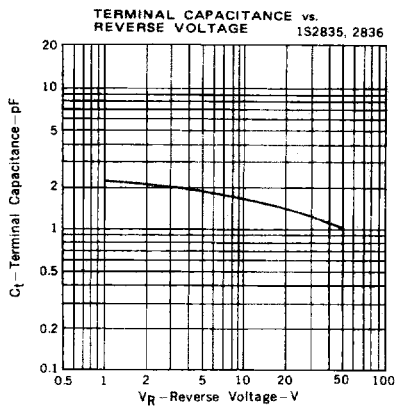
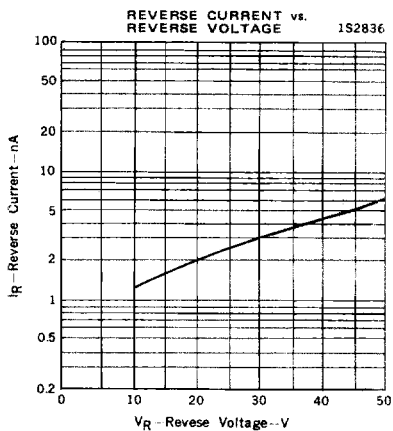
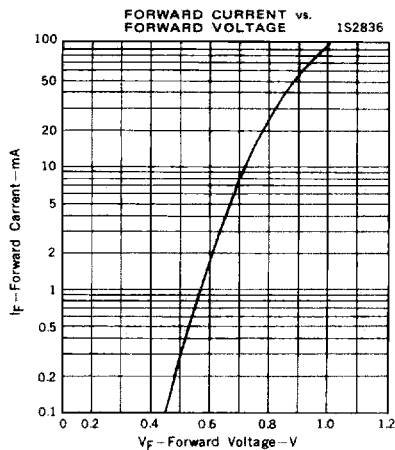
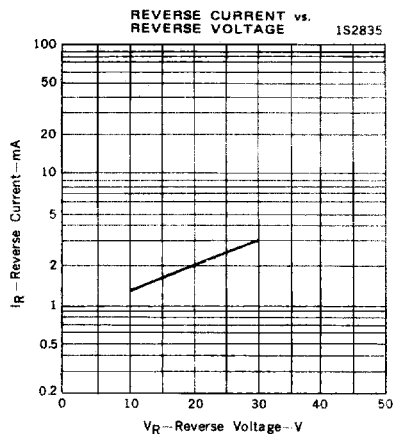
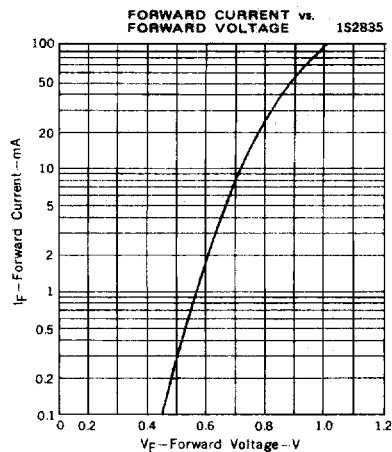
Junction to Ambient*	$R_{th(j-a)}$	1.0	1.0	°C/mW
Junction to Ambient	$R_{th(j-a)}$	0.67	0.67	°C/mW

* Both diodes loaded simultaneously.

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	1S2835 (A3)			1S2836 (A4)			UNIT	TEST CONDITIONS
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
Forward Voltage	V_{F1}		0.72	1.0		0.72	1.0	V	$I_F = 10 \text{ mA}$
	V_{F2}		0.88	1.1		0.88	1.1	V	$I_F = 50 \text{ mA}$
	V_{F3}		1.0	1.2		1.0	1.2	V	$I_F = 100 \text{ mA}$
Reverse Current	I_R			0.1				μA	$V_R = 30 \text{ V}$
	I_R						0.1	μA	$V_R = 50 \text{ V}$
Capacitance	C_t		2.5	4.0		2.5	4.0	pF	$V_R = 0, f = 1.0 \text{ MHz}$
Reverse Recovery Time	t_{rr}			4.0			4.0	ns	See Test Circuit.

TYPICAL ELECTRICAL CURVES ($T_a = 25^\circ\text{C}$)



REVERSE RECOVERY TIME (t_{rr}) TEST CIRCUIT

